## **PATENT**

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Das et al.

Confirmation No.: 3570 Group Art Unit: 1762

Serial No.: 10/045,542

Examiner: Michael. E. Barr

Filed: October 26, 2001

METHOD OF FABRICATING AN OXIDE LAYER ON A SILICON

CARBIDE LAYER UTILIZING AN ANNEAL IN A HYDROGEN

**ENVIRONMENT** 

Mail Stop Non-Fee Amendment Commissioner for Patents Washington, DC 20231

## **AMENDMENT**

Sir:

Applicants respectfully request entry of the following amendment in the above-referenced application.

Amendments to the Specification begin on page 2 of this paper.